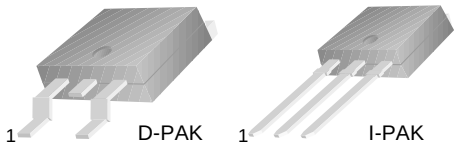
FAIRCHILD
SEMICONDUCTOR®

MJD112

D-PAK for Surface Mount Applications

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " - I " Suffix)
- Electrically Similar to Popular TIP112



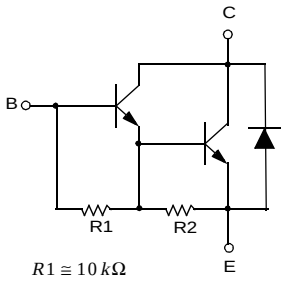
1.Base 2.Collector 3.Emitter

NPN Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	2	A
I_{CP}	Collector Current (Pulse)	4	A
I_B	Base Current	50	mA
P_C	Collector Dissipation (T_C=25°C)	20	W
	Collector Dissipation (T_a=25°C)	1.75	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 65 ~ 150	°C

Equivalent Circuit



$R1 \cong 10\,k\Omega$
$R2 \cong 0.6\,k\Omega$

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V_{CEO}(sus)	Collector-Emitter Sustaining Voltage	I_C = 30mA, I_B = 0	100		V
I_{CEO}	Collector Cut-off Current	V_{CE} = 50V, I_B = 0		20	µA
I_{CBO}	Collector Cut-off Current	V_{CB} = 100V, I_B = 0		20	µA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V, I_C = 0		2	mA
h_{FE}	* DC Current Gain	V_{CE} = 3V, I_C = 0.5A V_{CE} = 3V, I_C = 2A V_{CE} = 3V, I_C = 4A	500 1000 200	12K	
V_{CE}(sat)	* Collector-Emitter Saturation Voltage	I_C = 2A, I_B = 8mA I_C = 4A, I_B = 40mA		2 3	V V
V_{BE}(sat)	* Base-Emitter Saturation Voltage	I_C = 4A, I_B = 40mA		4	V
V_{BE}(on)	* Base-Emitter ON Voltage	V_{CE} = 3A, I_C = 2A		2.8	V
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.75A	25		MHz
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0 f = 0.1MHz		100	pF

* Pulse Test: PW≤300µs, Duty Cycle≤2%

Typical Characteristics

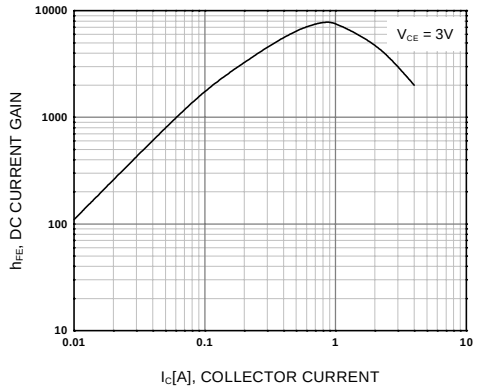


Figure 1. DC current Gain

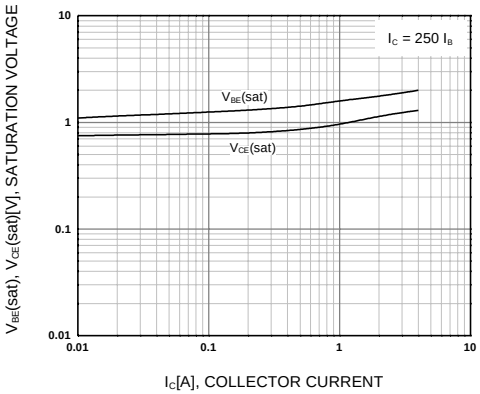


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

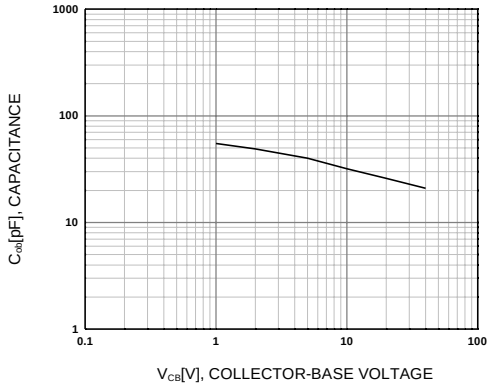


Figure 3. Collector Output Capacitance

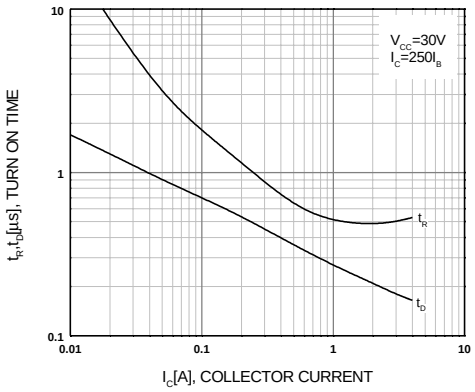


Figure 4. Turn On Time

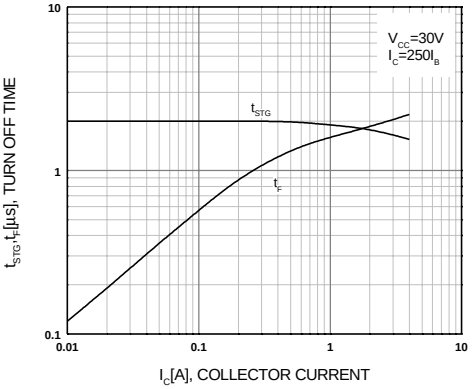


Figure 5. Turn Off Time

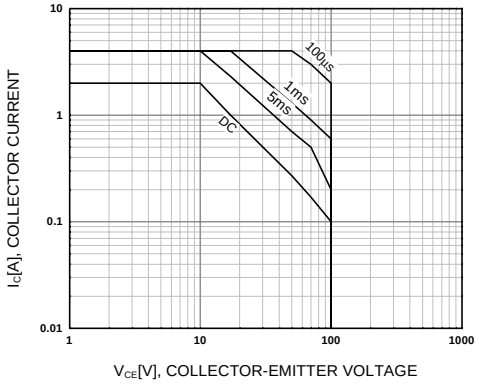


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

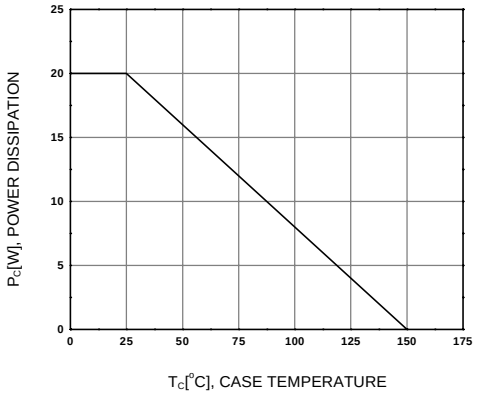
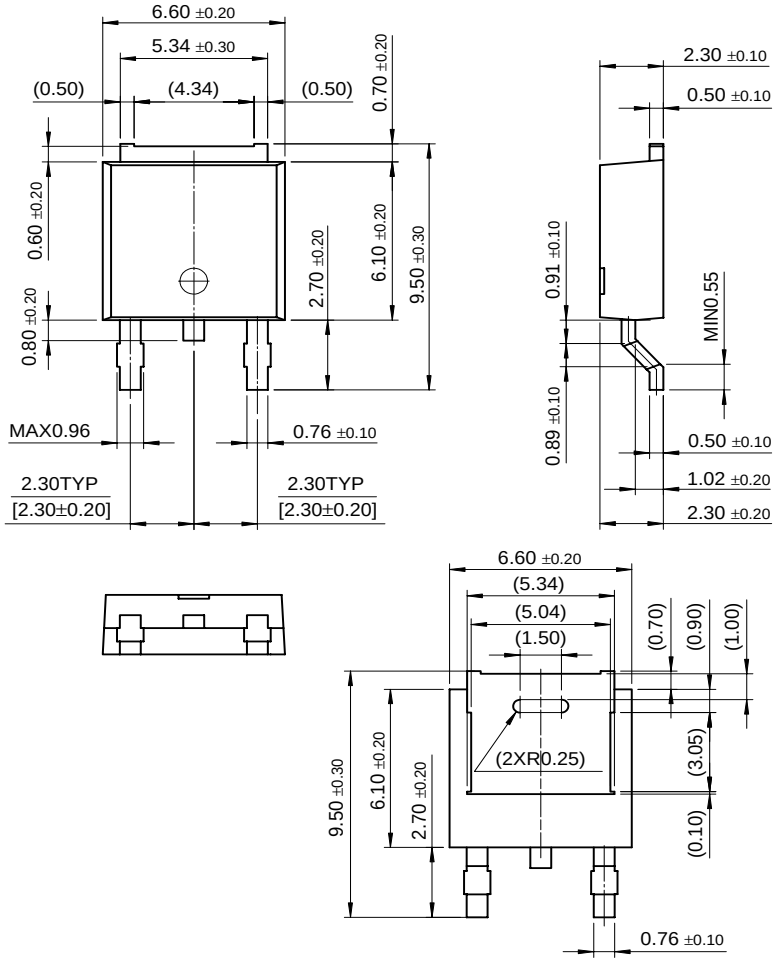


Figure 7. Power Derating

Package Demensions

D-PAK



Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	OPTOPLANAR™	STAR*POWER™
Bottomless™	FASTr™	PACMAN™	Stealth™
CoolFET™	FRFET™	POP™	SuperSOT™-3
CROSSVOLT™	GlobalOptoisolator™	Power247™	SuperSOT™-6
DenseTrench™	GTO™	PowerTrench®	SuperSOT™-8
DOME™	HiSeC™	QFET™	SyncFET™
EcoSPARK™	ISOPLANAR™	QS™	TruTranslation™
E^2CMOS™	LittleFET™	QT Optoelectronics™	TinyLogic™
EnSigna™	MicroFET™	Quiet Series™	UHC™
FACT™	MICROWIRE™	SLIENT SWITCHER®	UltraFET®
FACT Quiet Series™	OPTOLOGIC™	SMART START™	VCX™

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

MJD112
NPN Silicon Darlington Transistor

Contents

Datasheet
Download this datasheet

PDF

e-mail this datasheet

[E-

This page Print version

Related Links

Request samples

How to order products

Product Change Notices (PCNs)

Support

Distributor and field sales representatives

Quality and reliability

Design tools

Features

- High DC Current Gain
- Built-in Damper Diode at E-C
- Load Formed for Surface Mount Application (No Suffix)
- Straight Lead (I-PAK,"-I"Suffix)
- Electrically Similar to Popular TIP112

back to top

Applications

D-PAK for Surface Mount

back to top

Product status/pricing/packaging

Product	Product status	Package type	Leads	Packing method
MJD112TF	Full Production	TO-252(DPAK)	2	TAPE REEL

back to top